

BU407D

SILICON NPN TRIPLE DIFFUSED TYPE (PCT PROCESS)

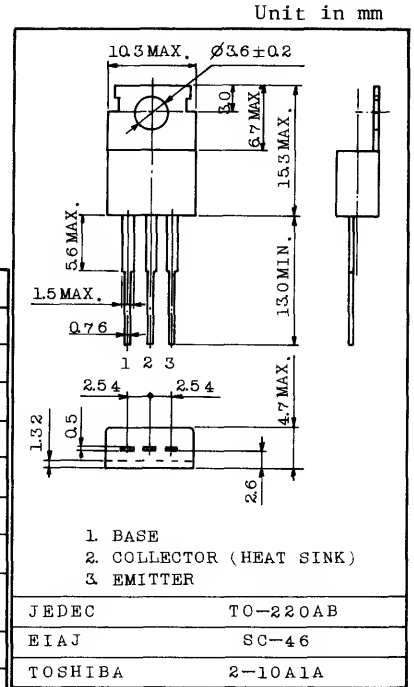
TV HORIZONTAL DEFLECTION OUTPUT APPLICATIONS.
HIGH VOLTAGE SWITCHING APPLICATIONS.

FEATURES:

- . Built in Damper Type
- . High Collector Current Capability
- . High Collector Power Dissipation Capability

MAXIMUM RATINGS (Ta=25°C)

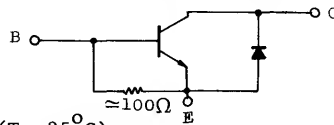
CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V _{CB0}	330	V
Collector-Emitter Voltage	V _{CE0}	150	V
Emitter-Base Voltage	V _{EB0}	6	V
Collector Current	DC	I _C	7 A
	Repetitive	I _{CM}	10 A
	Peak	I _{CP}	15 A
Base Current (Repetitive)	I _{BM}	2	A
Collector Power Dissipation (T _c =25°C)	P _C	60	W
Junction Temperature	T _j	150	°C
Storage Temperature Range	T _{stg}	-55 ~ 150	°C



Mounting Kit No. AC75

Weight : 1.9g

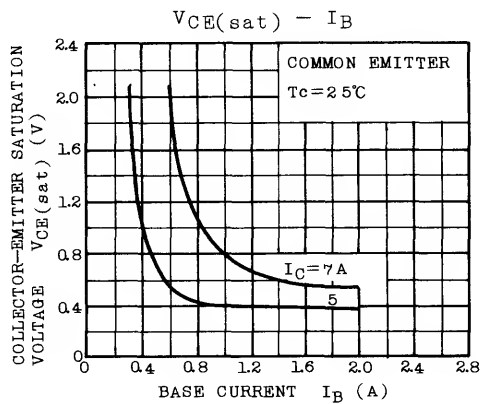
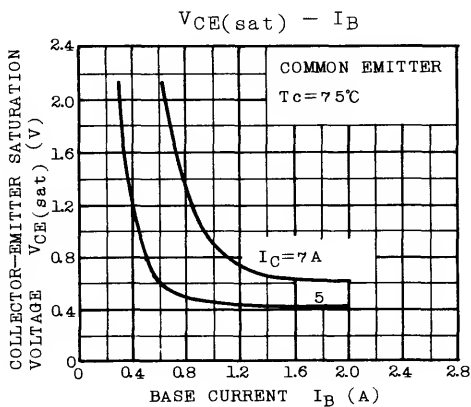
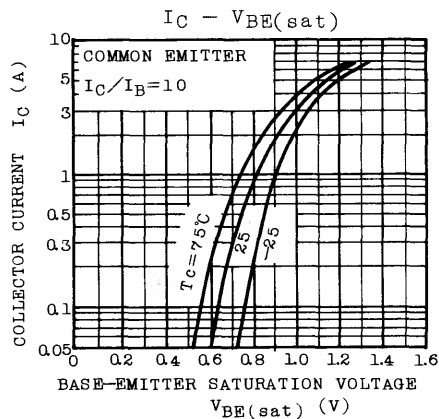
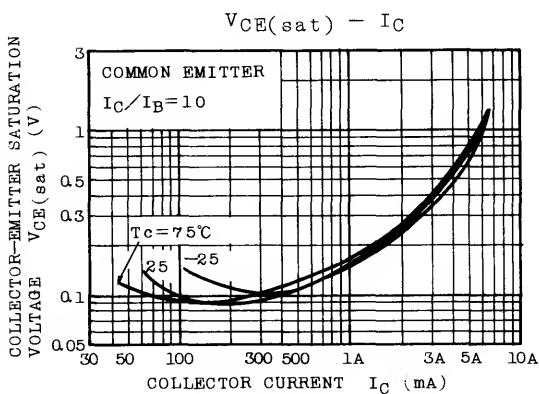
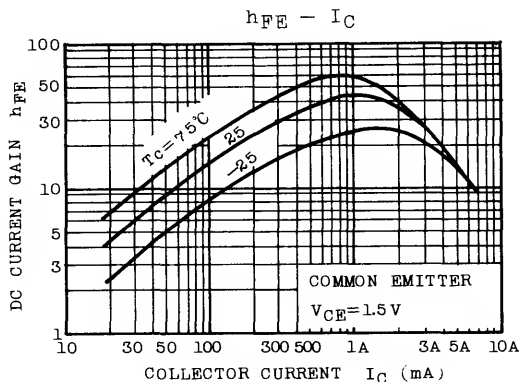
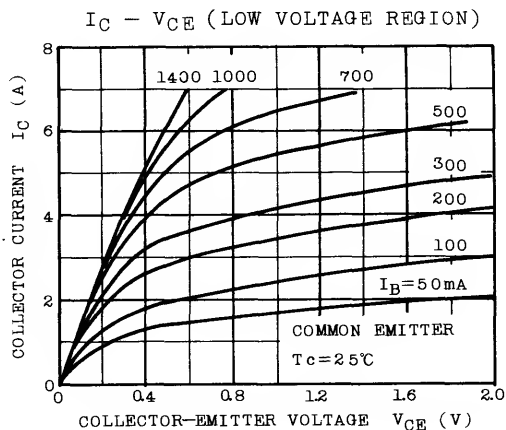
EQUIVALENT CIRCUIT



ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I _{CEs}	V _{CE} =250V, V _{BE} =0	-	-	1.0	mA
Collector-Emitter Sustaining Voltage	V _{CE0(SUS)}	I _C =0.1A, L=50mH	150	-	-	V
Collector-Base Breakdown Voltage	V _{(BR)CBO}	I _C =1mA, I _E =0	330	-	-	V
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	I _E =0.1A, I _C =0	6	-	-	V
DC Current Gain	h _{FE}	V _{CE} =1.5V, I _C =5A	10	-	-	
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _C =5A, I _B =0.5A	-	-	1.5	V
Base-Emitter Saturation Voltage	V _{BE(sat)}	I _C =5A, I _B =0.5A	-	-	1.5	V
Forward Voltage (Diode)	-V _F	I _C =-6A	-	-	1.8	V
Fall Time	t _f	I _{CP} =5A, I _{B1} =-I _{B2} =0.5A	-	-	1.0	μS
Transition Frequency	f _T	V _{CE} =10V, I _C =0.2A	-	18	-	MHz

TOSHIBA CORPORATION



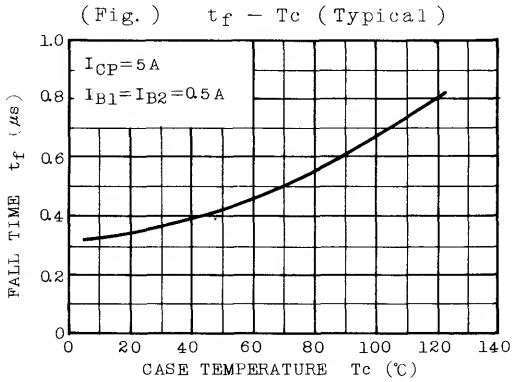
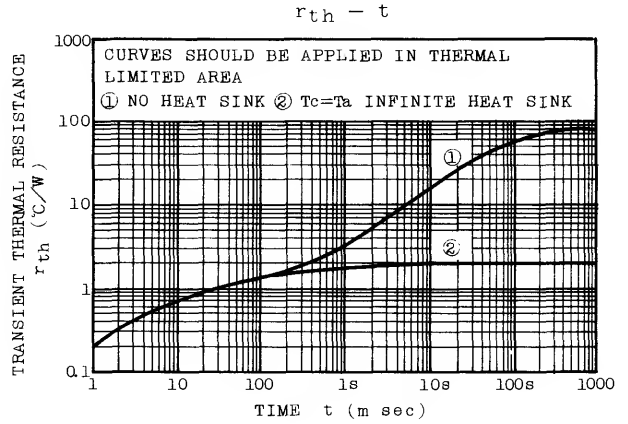
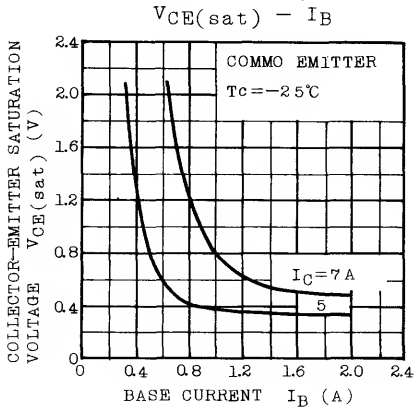


Fig. TEST CIRCUIT

